



Hong Yan et al.: "Scaling the Si MOSFET: From Bulk to SOI to Bulk", IEEE Transactions on Electron Devices, Vol. 39, No. 7, July 1992, pages 1704 – 1711;

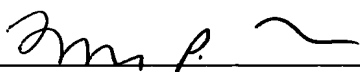
Thompson et al.: "MOS Scaling: Transistor Challenges for the 21st Century" Intel Technology Journal Q3'98, pages 1 – 19;

Curello et al.: "Beam-power heating effect on the synthesis of graded composition epitaxial $\text{Si}_{1-x}\text{Ge}_x$ alloy layers" Elsevier Science B.V., 1997, Nuclear Instruments and Methods in Physics Research B 129, pages 377 - 386.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the Applicants.

Respectfully submitted,

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